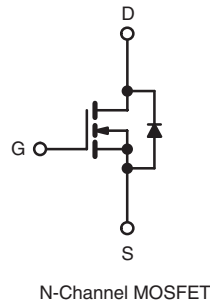
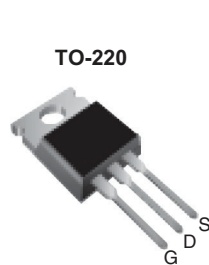


## Power MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V)	800
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$   3.0
$Q_g$ (Max.) (nC)	78
$Q_{gs}$ (nC)	9.6
$Q_{gd}$ (nC)	45
Configuration	Single



### FEATURES

- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available



### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION	
Package	TO-220
Lead (Pb)-free	IRFBE30PbF SiHFBE30-E3
SnPb	IRFBE30 SiHFBE30

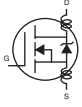

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	800	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current	$V_{GS}$ at 10 V	$I_D$	$T_C = 25\text{ }^\circ\text{C}$	A
			$T_C = 100\text{ }^\circ\text{C}$	
Pulsed Drain Current <sup>a</sup>		$I_{DM}$	16	
Linear Derating Factor			1.0	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy <sup>b</sup>		$E_{AS}$	260	mJ
Repetitive Avalanche Current <sup>a</sup>		$I_{AR}$	4.1	A
Repetitive Avalanche Energy <sup>a</sup>		$E_{AR}$	13	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	125	W
Peak Diode Recovery $dV/dt^c$		$dV/dt$	2.0	V/ns
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s		300 <sup>d</sup>	
Mounting Torque	6-32 or M3 screw		10	
			1.1	N · m

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 29\text{ mH}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = 4.1\text{ A}$  (see fig. 12).
- $I_{SD} \leq 4.1\text{ A}$ ,  $dI/dt \leq 100\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 600$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

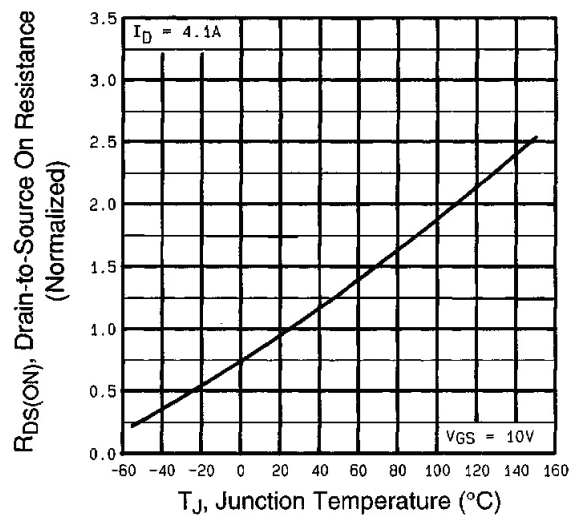
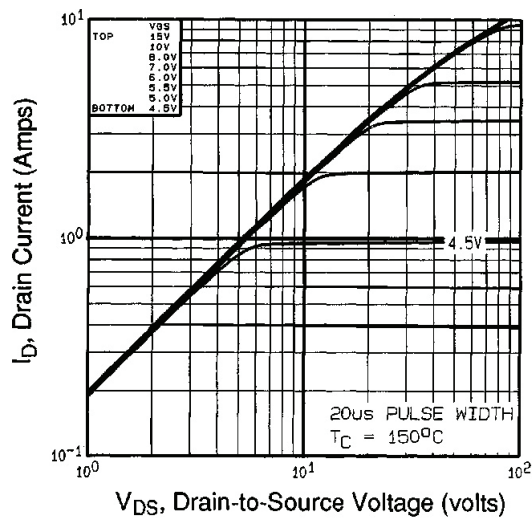
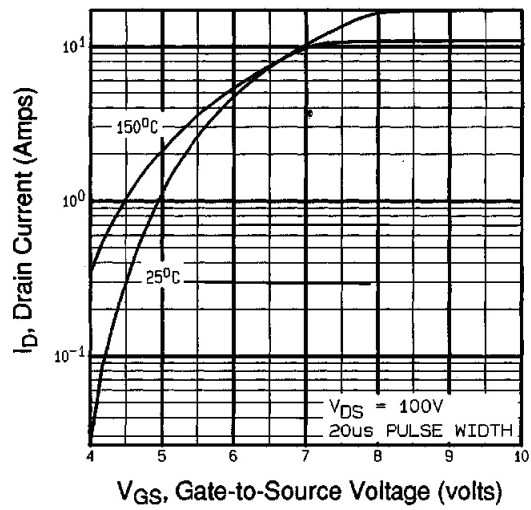
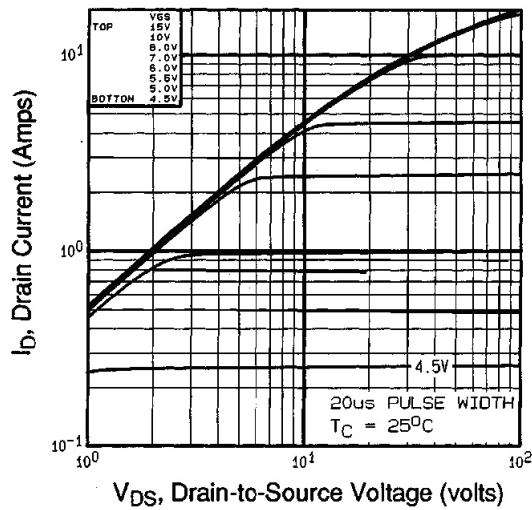
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.0	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	800	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$	-	0.9	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	-	-	100	$\mu\text{A}$
		$V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}^b$	-	-	3.0	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 100\text{ V}, I_D = 2.5\text{ A}^b$	2.5	-	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$	-	1300	-	pF
Output Capacitance	$C_{oss}$		-	310	-	
Reverse Transfer Capacitance	$C_{rss}$		-	190	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 4.1\text{ A}, V_{DS} = 400\text{ V}, \text{ see fig. 6 and 13}^b$	-	-	78	nC
Gate-Source Charge	$Q_{gs}$		-	-	9.6	
Gate-Drain Charge	$Q_{gd}$		-	-	45	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 4.1\text{ A}, R_G = 12\text{ }\Omega, R_D = 95\text{ }\Omega, \text{ see fig. 10}^b$	-	12	-	ns
Rise Time	$t_r$		-	33	-	
Turn-Off Delay Time	$t_{d(off)}$		-	82	-	
Fall Time	$t_f$		-	30	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	$L_S$		-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	4.1	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	16	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 4.1\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.8	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 4.1\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	480	720	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	1.8	2.7	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



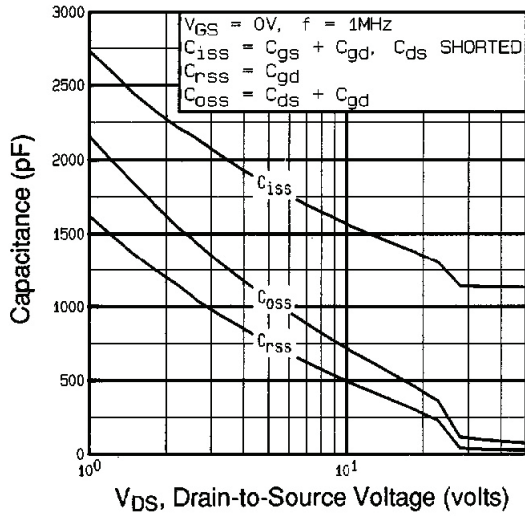


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

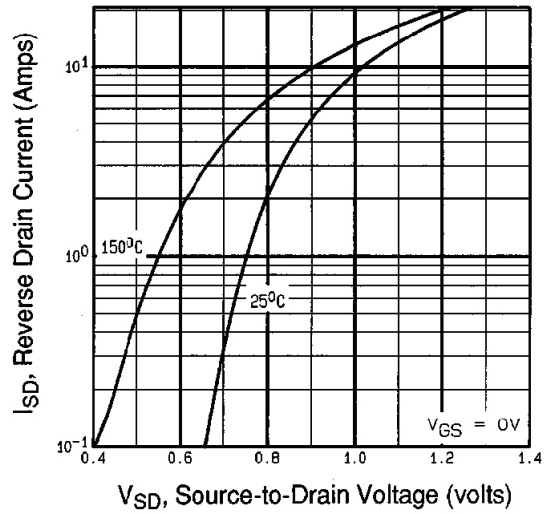


Fig. 7 - Typical Source-Drain Diode Forward Voltage

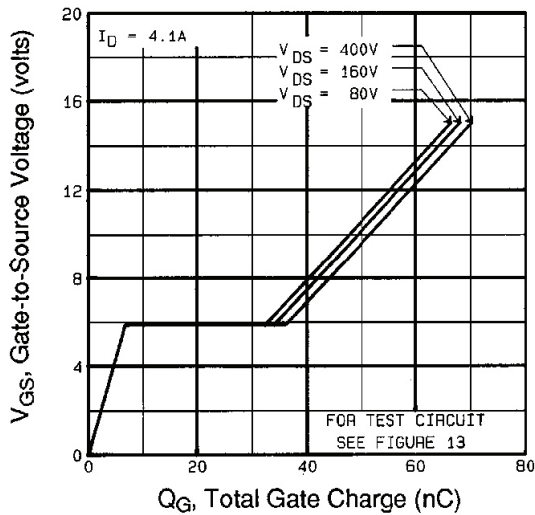


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

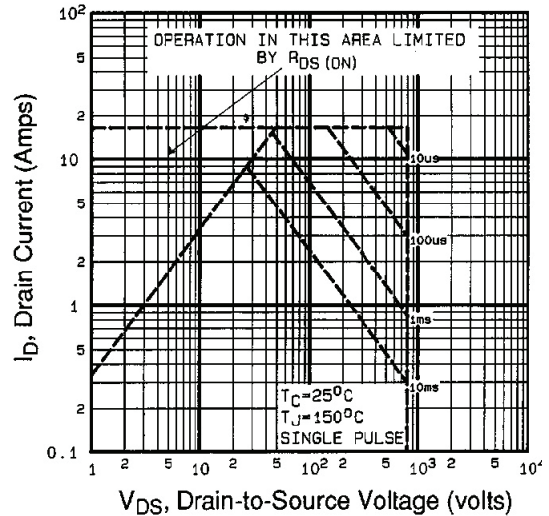


Fig. 8 - Maximum Safe Operating Area

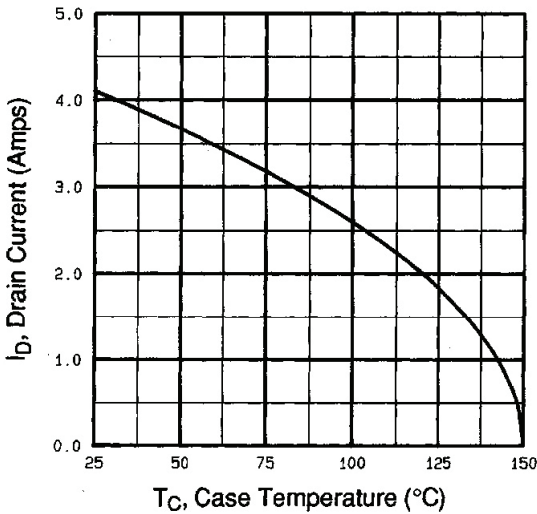


Fig. 9 - Maximum Drain Current vs. Case Temperature

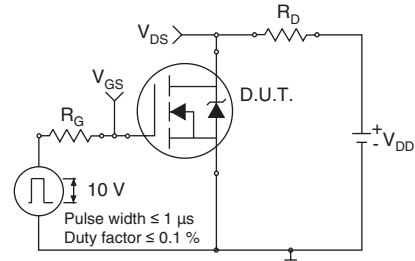


Fig. 10a - Switching Time Test Circuit

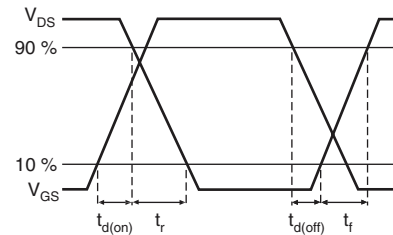


Fig. 10b - Switching Time Waveforms

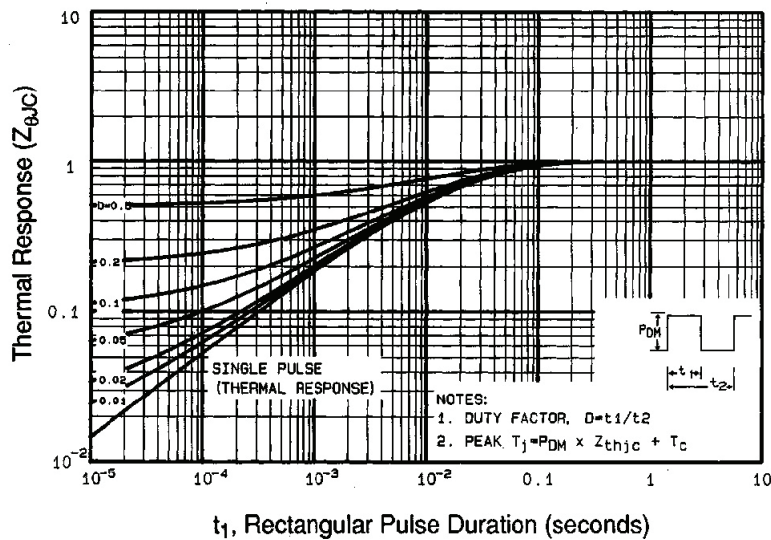


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

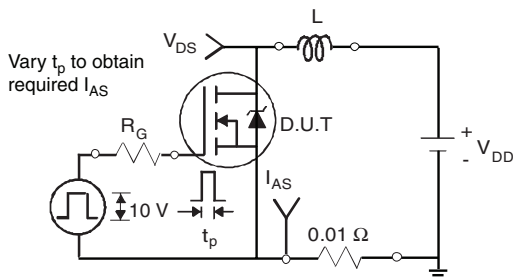


Fig. 12a - Unclamped Inductive Test Circuit

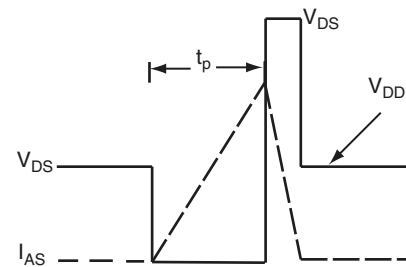


Fig. 12b - Unclamped Inductive Waveforms

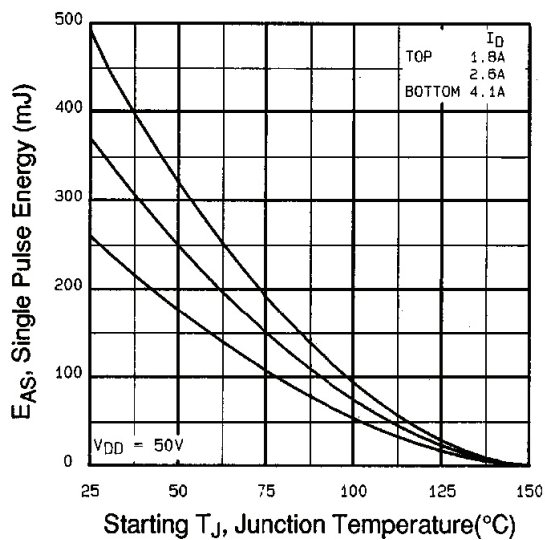


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

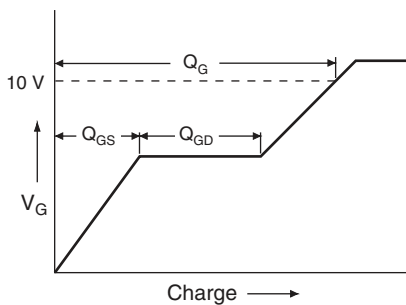


Fig. 13a - Basic Gate Charge Waveform

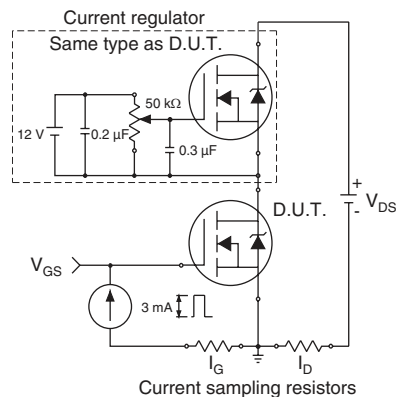
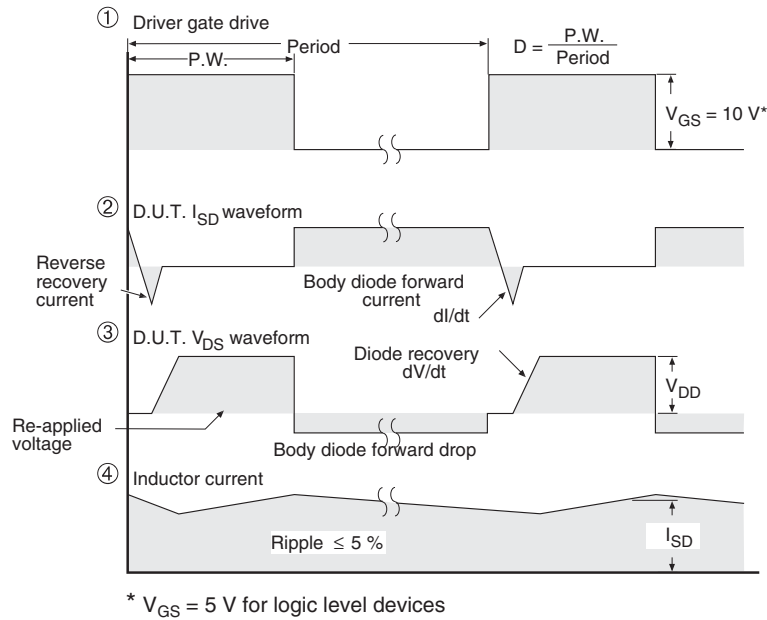
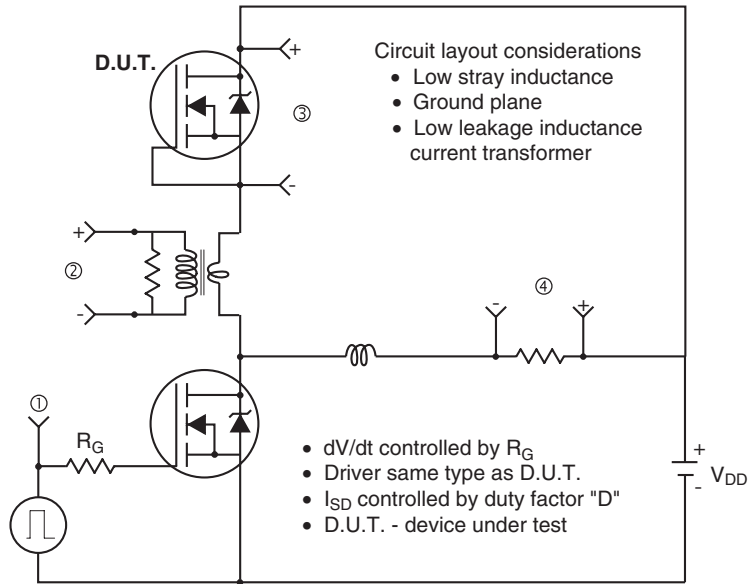


Fig. 13b - Gate Charge Test Circuit

## Peak Diode Recovery $dV/dt$ Test Circuit



**Fig. 14 - For N-Channel**

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